

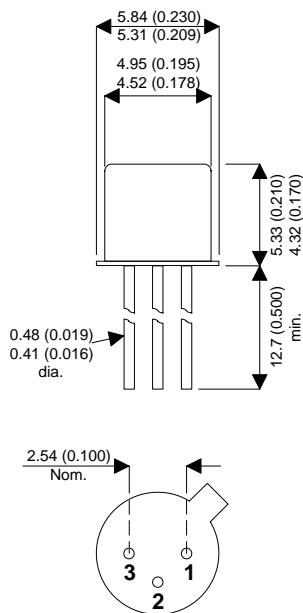


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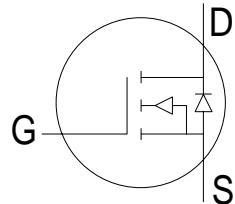
VN10K-T018

MECHANICAL DATA

Dimensions in mm (inches)



N-CHANNEL ENHANCEMENT MODE MOSFET



TO18 PACKAGE Underside View

PIN 1 - Source

PIN 2 - Gate

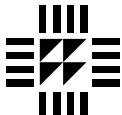
PIN 3 - Drain & Case

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25^\circ\text{C}$ unless otherwise stated)

V_{DS}	Drain – Source Voltage	60V
V_{GS}	Gate – Source Voltage	+15 , -0.3 V
I_D	Continuous Drain Current @ $T_{amb} = 25^\circ\text{C}$	0.17A
	@ $T_{amb} = 100^\circ\text{C}$	0.11A
I_{DM}	Pulsed Drain Current ¹	1.0A
P_D	Power Dissipation @ $T_{amb} = 25^\circ\text{C}$	1.5W
	@ $T_{amb} = 100^\circ\text{C}$	0.12W
T_{STG}, T_J	Maximum Junction and Storage Temperature Range	-55 to 150°C

NOTE:

1) Repetitive Rating: Pulse Width limited by maximum junction temperature.



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ELECTRICAL RATINGS ($T_{amb} = 25^\circ C$ unless otherwise stated)

Characteristic	Test Conditions			Min.	Typ.	Max.	Unit
STATIC CHARACTERISTICS							
BV_{DSS}	Drain – Source Breakdown Voltage	$V_{GS} = 0V$	$I_D = 100\mu A$	60	120		V
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$	$I_D = 1mA$	0.8	1.4	2.5	
I_{GSS}	Gate – Source Leakage Current	$V_{DS} = 0V$	$V_{GS} = 15V$		1	100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 48V$	$V_{GS} = 0V$		0.7	10	μA
			$T_J = 125^\circ C$		3	500	
$I_{D(ON)}$	On State Drain Current ¹	$V_{DS} = 10V$	$V_{GS} = 10V$	750	1000		mA
$R_{DS(ON)}$	Static Drain – Source On-State Resistance ¹	$V_{GS} = 5V$	$I_D = 0.2A$		4	7.5	Ω
		$V_{GS} = 10V$	$I_D = 0.5A$		3	5	
			$T_J = 125^\circ C$		5.6	9	
g_{fs}	Forward Transconductance ¹	$V_{DS} = 10V$	$I_D = 0.5A$	100	300		mS
g_{os}	Common Source Output Conductance	$V_{DS} = 7.5V$	$I_D = 50mA$		200		μS
DYNAMIC CHARACTERISTICS							
C_{iss}	Input capacitance	$V_{GS} = 0V$			38	60	pF
C_{oss}	Output capacitance	$V_{DS} = 25V$			16	25	
C_{rss}	Reverse transfer capacitance	$f = 1MHz$			2	5	
SWITCHING CHARACTERISTICS							
t_{on}	Turn-on Time	$V_{DD} = 15V$	$R_L = 23\Omega$		7	10	ns
t_{off}	Turn-off Time	$I_D = 0.6A$	$R_G = 25\Omega$		9	10	
		$V_{GEN} = 10V$					

NOTES:

- 1) Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2\%$

THERMAL CHARACTERISTICS

Characteristic	Min.	Typ.	Max.	Unit
$R_{\theta JA}$			400	$^\circ C/W$